Superconductivity and crystalline electric eld e ects in the lled skutterudite series $Pr(Os_{1} Ru_{x})_{4}Sb_{12}$

N.A. Frederick, T.D.Do, P.-C. Ho, N.P. Butch, V.S. Zapf, and M.B. Maple
Department of Physics and Institute for Pure and Applied Physical Sciences,
University of California at San Diego, La Jolla, CA
(Dated: March 22, 2024)

X-ray powder di raction, magnetic susceptibility (T), and electrical resistivity (T) measurements were made on single crystals of the led skutterudite series $Pr(0 s_{1-x}Ru_x)_4Sb_{12}$. One end of the series (x = 0) is a heavy ferm ion superconductor with a superconducting critical temperature $T_c=1.85$ K, while the other end (x = 1) is a conventional superconductor with $T_c=1$ K. The lattice constant a decreases approximately linearly with increasing Ru concentration x. As Ru (Os) is substituted for Os (Ru), T_c decreases nearly linearly with substituent concentration and exhibits a minimum with a value of $T_c=0.75$ K at x=0.6, suggesting that the two types of superconductivity compete with one another. Crystalline electric eld (CEF) elects in T_c (T) and (T) due to the splitting of the Pr^{3+} nine-fold degenerate H und's rule $T_c=0.16$ M multiplet are observed throughout the series, with the splitting between the ground state and the rest excited state increasing monotonically as x increases. The to the $T_c=0.16$ decreases are another to data are consistent with a $T_c=0.16$ doublet ground state for all values of x, although reasonable to can be obtained for a $T_c=0.16$ ground state for x values near the end member compounds (x = 0 or x = 1).

PACS numbers: 7127.+a,7425Fy,7425Ha,74.62Dh

I. INTRODUCTION

The led skutterudite compound PrO \$Sb₁₂ was recently discovered to be the rst Pr-based heavy ferm ion superconductor, with a superconducting transition temperature $T_c = 1.85 \text{ K}$ and an e ective mass m where m_e is the free electron mass. Features in the dc magnetic susceptibility dc (T), speci c heat C (T), electrical resistivity (T), and inelastic neutron scattering (INS) can be associated with the thermally dependent population of the ninefold degenerate $Pr^{3+} J = 4$ Hund's rule multiplet split by a cubic crystalline electric eld (CEF). These data suggest that the ground state of PrOs₄Sb₁₂ is a 3 doublet, separated from a 5 triplet rst excited state by 10 K 1 , The possibility of a 1 singlet ground state has also been put forward based on other measurements, 3,4 some of which also consider tetrahedral sym m etry operators in their calculations of the CEF Ham iltonian of PrOs₄Sb₁₂. It has been proposed that the superconductivity in PrOs₄Sb₁₂ may be due to quadrupolar uctuations, a claim that has been supported by SR^6 and $Sb-NQR^7$ m easurem ents, which indicate a strong-coupling isotropic energy gap of 2 5k_B T_c. O ther intriguing e ects are seen in PrO §Sb₁₂, including multiple superconducting transitions8,9,10 and phases, 11 and an ordered phase that is observed in high magnetic elds and low temperatures. This high ordered phase (HFOP), which is seen in measurements of $(T)_{1}^{12} C (T)_{3}^{3,9}$ m agnetization M $(T)_{1}^{13}$ therm alexpansion $(T)_{1}^{10}$ and magnetostriction $(T)^{14}$ in a magnetic eld H, as well as measurements of (H) isotherm s_{r}^{13} appears to be related to the crossing of the CEF energy levels in magnetic elds. In addition, neutron di raction experim ents⁴ indicate the presence of quadrupolar e ects in the HFOP, analagous to those seen in PrPb. 16

PrO s_4Sb_{12} has proven to be a unique compound, and will continue to provide a fertile area of research for many years.

The isostructural compound PrRu₄Sb₁₂ displays superconductivity below T_c 1:0 K and possesses an electronic speci c heat coe cient approximately 5 to 10 tim es smaller than PrOs₄Sb₁₂, identifying it at as a conventional m etal, or at most a borderline heavy ferm ion m etal. 17 It was previously reported, based on m easurements of $_{dc}$ (T), to possess a $_{1}$ ground state and a 4 triplet state 70 K above the ground state. 17 A later m easurem ent of (T) also supported this CEF level schem e. 18 P rR u_4 Sb $_{12}$ appears to be a BCS-like weak-coupling superconductor, with an isotropic s-wave energy gap of 2 $3k_B T_{c}$, as determined from Sb-NQR m easurem ents. 19 At the present time, no quadrupolar effects or features resembling the HFOP seen in PrOs4Sb12 have been reported in PrRu₄Sb₁₂.

The substitution of PrR u_4 Sb $_{12}$ into PrO s_4 Sb $_{12}$ to form Pr(O s_1 x Rux) $_4$ Sb $_{12}$ was undertaken to investigate the evolution of the superconductivity, the CEF energy level scheme, and the heavy ferm ion state with Ru-doping, and to investigate the relationship, if any, between these three phenomena. The present study focuses on measurements of (x;T) and (x;T), which have revealed the x-dependencies of T_c and the splitting between the CEF ground state and the rst excited state. We are also in the process of investigating the heavy ferm ion state via measurements of C(T), and the upper critical eld H_{c2} (T) through measurements of (T;H) (which will also reveal the x-dependence of the HFOP), and will report these results in a future publication.

II. EXPERIM ENTAL DETAILS

Single crystals of Pr(O s₁ $_{\rm X}$ Ru $_{\rm X}$)₄Sb₁₂ were grown using an Sb ux m ethod. The elements (Ames 5N Pr, Colonial M etals 3:5N O s and 3N Ru, and Alfa Aesar 6N Sb) were sealed under 150 Torr Ar in a carbon-coated quartz tube in the ratio 1:4 4x:4x:20, heated to 1050 C at 50 C/hr, then cooled at 2 C/hr to 700 C. The sam ples were then removed from the furnace and the excess Sb was spun o in a centrifuge. The crystals were removed from the leftover ux by etching with dilute A qua Regia (HClHNO3H20 = 1:1:3).

X-ray powder di raction measurements were made at room temperature using a Rigaku D/MAX B x-ray machine. The only signi cant im purities in any of the sam ples were identied with free Sb that was still attached to the crystals. Each P r (O $s_{1 \times}$ R u_{x})₄Sb₁₂ sam ple crystallized in the LaFe $_4$ P $_{12}$ structure 20 w ith a lattice constant a that decreased roughly linearly with increasing Ru concentration x, as displayed in Fig. 1. A silicon standard was used in order to achieve a more accurate determination of the lattice constant. M easurem ents of dc vs tem perature T were made in a magnetic eld H of 0:5 tesla between 1:8 and 300 K in a commercialQuantum Design superconducting quantum interference device (SQUD) m agnetom eter. M easurem ents of and ac were made as a function of T down to 12 K in a 4He cryostat and, for several of the samples, down to 0:1 K in a ${}^{3}\text{He}^{-4}\text{He}$ dilution refrigerator.

III. RESULTS

A. M agnetic Susceptibility

D isplayed in the main portion of Fig. 2 is a plot of the dc magnetic susceptibility dc as a function of temperature T for single crystals of $Pr(Os_1 \times Ru_x)_4Sb_{12}$ with various values of x. Above T 100 K, the inverse m agnetic susceptibility 1= dc is linear, indicating Curie-Weiss behavior. The data have been corrected for excess Sb by assuming that the high temperature e ective moment, e , of Pr should be equal to the Hund's rule free ion value of 3.58 B for Pr^{3+} , where B is the Bohrm agneton. Any deviation from this value was attributed to free Sb inclusions in the Pr(O $s_{1\ x}$ Ru_x)₄Sb₁₂ crystals. The most signicant e ect on dc from this correction was not the small diam agnetic Sb signal but instead the change in overall scaling due to the di erence in mass used to calculate dc in units of cm $^3/m$ ol from the raw m agnetization data. The calculated percentages of mass attributed to Sb out of the total sample volume for all values of x are listed in Table I. The estimated value of the Sb mass depends slightly on the CEF ground state used to make the t correction; only the values for a 3 ground state are given for sim plicity.

A llofthe Pr(0 s₁ $_{\rm x}$ Ru $_{\rm x}$) $_4$ Sb $_{12}$ sam ples exhibit features (peaks or plateaus) in $_{\rm dc}$ that can be attributed to CEF

e ects. These features are the focus of the two insets in Fig. 2. The low temperature $_{\rm dc}$ data for the samples from x=0 to x=0.4 are shown in Fig. 2(a), while Fig. 2(b) similarly displays data for the samples from x=0.5 to x=1. An explanation of the ts used to determ ine the CEF parameters from the $_{\rm dc}$ data, as well as the parameters them selves, is given in section IV B.

Low temperature (< 2 K) ac magnetic susceptibility ac vsT data for Pr(Os_{1 x} Ru_x)₄Sb₁₂ are shown in Fig. 3. A sharp diam agnetic transition can be seen for all values of x, indicating the presence of superconductivity. The superconducting critical tem perature Tc for each concentration was determined from the data displayed in Fig. 3 as the m idpoint of the diam agnetic transition. A plot of T_c vs x is displayed in Fig. 6, and is discussed further in section IV A. An additional feature of note is the steplike structure that appears in the ac data for PrO s_4Sb_{12} . Since double superconducting transitions have been observed in speci c heat and therm alexpansion measurem ents on both collections of single crystals and individual single crystals, 8,9,10 it is reasonable to assume that this step in the diam agnetic transition for PrOs₄Sb₁₂ is also due to an intrinsic second superconducting phase instead of a variation of T_c throughout the multiple crystals used in the ac measurements. None of the other concentrations display signi cant structure in their superconducting transitions, although the transitions for x = 0.3 and x = 0.4 are much wider than for the other concentrations. This may be due to a variation of Tc between individual crystals for these two concentrations.

B. Electrical Resistivity

Fig. 4 displays high-tem perature electrical resistivity vs T data for Pr(O $s_{1\ x}$ Ru $_{x}$) $_{4}$ Sb $_{12}$ for various values of xbetween 0 and 1. The values of at room temperature, (300 K), and the extrapolated values of at zero tem perature from ts to the (T) data based on calculations of (T) that incorporate CEF splitting of the Pr^{3+} J = 4 multiplet (see section IVB), (0K), are listed in Table I. Also listed in Table I is the residual resistivity ratio (RRR), de ned as (300 K)= (0 K). It is surprising that the RRR of $PrRu_4Sb_{12}$ is so much lower than that of PrOs₄Sb₁₂, since they are both stoichiom etric com pounds and would be expected to have a low residual resistivity. A previous m easurem ent of PrRu₄Sb₁₂ found (300 K) = 632cm and an RRR of 25_{l}^{17} in reasonable agreement with the data presented in this paper. The low RRR of $PrRu_4Sb_{12}$ is not presently understood.

The electrical resistivity of Pr(0 s₁ $_{\rm X}$ Ru_x)₄Sb₁₂ below T = 2 K is shown in Fig. 5. The data have been normalized to their values at 2 K in order to emphasize the superconducting transitions. The x = 0:7 sample did not display the onset of superconductivity down to the lowest measured temperatures and no data for this sample are shown in this plot; the heating due to large contact resistances in the x = 0:7 and x = 0:9 samples precluded

m easurem ents below 1 K. The superconducting transitions as determined from (T) are in reasonable agreement with those measured inductively (Fig. 3), and the plot of $T_{\rm c}$ vs x is discussed in the following section.

IV. ANALYSIS AND DISCUSSION

A. Superconductivity

The dependence of the superconducting transition temperature T_c on Ru concentration x for $Pr(0 s_{1 x} Ru_{x})_{4}Sb_{12}$ is shown in Fig. 6. Several concentrations have more than one data point associated with them, which are from measurements of dierent crystals. These additional measurements were not shown in Figs. 4 and 5 or listed in Table I in the interest of clarity. The RRRs were nearly identical for all crystals of a given concentration, with the exception of the x = 0.2sam ples where the crystal with the lowest T_c in Fig. 6 had an RRR about half of that measured for the other two x = 0.2 samples, one of which is listed in Table I. The vertical bars in Fig. 6 are a measure of the width of the superconducting transitions, taken to be the 10% and 90% values of the resistance change associated with the transition.

The trend of the T_c vs x data shown in Fig. 6 suggests a competition between the two dierent types of superconductivity seen in PrOs₄Sb₁₂ and PrRu₄Sb₁₂. This competition suppresses T_c from both ends, culm inating in a minimum of $T_c = 0.75$ K near x = 0.6. Speci c heat m easurem ents are in progress, and it will be interesting to see if the heavy ferm ion state can be correlated with T_c. The persistence of superconductivity throughout the series is unusual, as for heavy ferm ion f-electron superconductors both magnetic and nonmagnetic impurities generally produce relatively rapid depressions of T_c. When the impurity is of an element that would produce an isostructural superconducting com pound, the trend is not as clear. For example, the U $_1$ $_x$ La $_x$ Pd $_2$ A $_3$ system is similar to the Pr(O $s_{1 \times}$ Ru_x)₄Sb₁₂ system in that one end m em ber com pound, UPd2Al3, is a heavy ferm ion superconductor, while the other end member compound, $LaPd_2Al_3$, is a conventional BCS superconductor. Unlike $Pr(Os_1 \times Ru_x)_4Sb_{12}$, however, superconductivity is destroyed upon substitution on either end of the series.²¹ This persistence of superconductivity throughout of the $Pr(Os_{1 \times} Ru_{x})_{4}Sb_{12}$ system for all values of x is observed in the CeCo $_{1\ x}$ $\text{Ir}_{x}\,\text{In}_{5}$ series of compounds, which is also superconducting for all values of x. 22 This system 's sim ilarities to $Pr(Os_{1} Ru_{x})_{4}Sb_{12}$ end there, because both end m em ber com pounds (C eC oIn₅ and C eIrIn₅) are heavy ferm ion superconductors in which the superconductivity is believed to be magnetically mediated and to possess nodes in the energy gap (k).

This nodal energy gap structure may be in contrast with PrOs $_4$ Sb $_{12}$, where SR 6 and Sb-NQR 7 measurements indicate an isotropic energy gap, a condition which

could occur if the superconductivity in PrO s_4Sb_{12} was mediated by quadrupolar uctuations. It is also generally the case that superconductors with isotropic or nearly isotropic energy gaps are relatively insensitive to the presence of nonmagnetic impurities. Thus, the gradualdecrease of T_c, and the presence of superconductivity for all values of x in P r (O $s_{1 \times R} u_{x}$) $_{4}Sb_{12}$, provides further evidence for an isotropic energy gap and quadrupolar superconductivity in PrOs₄Sb₁₂, since PrRu₄Sb₁₂ also possesses an isotropic superconducting energy gap. 19 The m in im um in T_c near x = 0:6 could then be attributed to a shift from quadrupolarm ediated heavy ferm ion superconductivity to phonon mediated BCS superconductivity. On the other hand, therm al conductivity measurements of PrOs₄Sb₁₂ in a magnetic eld have been interpreted in terms of two distinct superconducting phases T plane, one with two point nodes in elds, and another with six point nodes in (k) at higher elds. Since no them al conductivity measurements were reported for elds below 0:3 T, the structure of (k) is not known below this eld. It is conceivable that, just as a magnetic eld induces a change from a state with two point nodes into a state with six point nodes, the state with two point nodes is itself induced from an isotropic zero- eld energy gap. Further measurem ents of the energy gap sym metry in zero and low m agnetic eld could shed light on this mystery.

${\tt B}$. C rystalline E lectric F ield E $\,$ ects

The $_{dc}$ (T) and (T) data for Pr(O $q_x Ru_x$) $_4 Sb_{12}$ were t to equations including CEF e ects, in a manner identical to that reported previously.^{1,15} The CEF equations were derived from the Hamiltonian of Lea, Leask and W olf (LLW). 24 In the LLW form alism, the CEF energy levels are given in terms of the parameters x_{LLW} and W , where $x_{\text{\tiny LLW}}$ is the ratio of the fourth and sixth order terms of the angular momentum operators and W is an overall energy scale factor. It was assumed that the CEF param etery which controls the tetrahedral Th crystalline sym metry contribution to the Hamiltonian was sm all; thus, the calculations were made for a cubic Oh crystalline sym metry. Assuming that y is small implies that the main contribution to the crystalline electric eld com es from the simple cubic transition metal sublattice (OsorRu), as opposed to the more complicated tetrahedral Sb sublattice. The dc (T) data for x be reasonably twith either a $_{3}$ or a $_{1}$ ground state and a 5 rst excited state. As x increases, the magnitude of the peak in dc decreases more rapidly than the tem perature $T_{m \ ax}$ at which the peak occurs. The peak also broadens until it resembles a hump. These changes with x make it unreasonable to ta 1 { 5 CEF energy level scheme to the higher x data, since for these data an energy level scheme with the correct $T_{m\ ax}$ makes the peak too sharp, while the correct hum p shape results in a $T_{m \ ax}$ that is too high. Thus, for the Pr(O $s_{1 \ x}$ Ru_x)₄Sb₁₂

sam ples with x 0.2, a $_3$ ground state best approximated the data. An example of a twith a $_3$ ground state for x = 0.6 is shown in Fig. 7(a). A plot of the splitting between the ground state and the rst excited state vs x is shown in Fig. 8, including all reasonable ts of the $_{\rm dc}$ (T) data.

The Pr(O $s_{1} \times Ru_{x}$)₄Sb₁₂ sam ples with x 0:6 all display uptums in $_{dc}$ (T) at the lowest temperatures (inset (b) in Fig. 2). If these uptums are due to the splitting of the CEF energy levels in a small magnetic eld H, then it is expected that they would be more visible in the sam ples with large x (more Ruthan Os), where dc is smaller at low tem peratures compared to the small x (more Os than Ru) data. The samples with x 0:75, including PrRu₄Sb₁₂, also display structure in these uptums that appear to be an additional peak near 5 K superim posed on the broad CEF hump, near the temperature of the CEF peak in PrO s4Sb12. The sm ooth progression of both the lattice parameter a and $T_{\rm c}$ indicates that there is no m acroscopic phase separation of Pr(Os_{1 x} Ru_x)₄Sb₁₂ into PrO s_4Sb_{12} and PrRu $_4Sb_{12}$. However, it is possible that the peak-like structure could be due to inhom ogeneous alloying of 0 s and R u on an atom ic scale, wherein each Pr3+ ion sees a distribution of 0 sor Ru atom s, leading to a variation in the CEF throughout the crystal. Unfortunately, this possibility would be dicult to establish in the current experim ents. The low-tem perature uptum, especially in PrRu₄Sb₁₂, could be attributed to either CEF splitting in H or param agnetic im purities, both of which could produce a low-tem perature increase in dc.

Takeda et al. reported that PrRu₄Sb₁₂ had a 1 singlet ground state and a 4 triplet state, a CEF con guration that exhibits a plateau in dc at low tem peratures.¹⁷ In the current experim ent, the x = 0.9and x = 1 samples are the only ones in which a plateau is observed. In addition, while the other samples with 0:85 have their peaks reasonably well described by a $_3$ ground state, the t predicts a saturation at T = 0 K that is much lower than is observed in the data. However, the low-T uptum could be responsible for disguising both the maximum in x = 0.9 and x = 1 and the low temperature saturation observed in the other high Ru concentration samples. Accordingly, all the Pr(O $s_1 \times Ru_x$)₄Sb₁₂ data with x 0:85 were t assuming both a 3 CEF energy levelscheme and a 1 4 scheme, ignoring the low-tem perature uptum; the x = 0.85 ts are shown in Fig. 7 (b). Both ts are represented in the splitting between the ground state and $\,$ rst excited state $\,$ Eqs $_{1es}$ vs x plot of Fig. 8; the results from all ts are also listed in Table I.

The electrical resistivity (T) of Pr(O s $_{\rm x}$ Ru $_{\rm x}$) $_4$ Sb $_{12}$ was t by a combination of scattering from impurities, the atomic lattice (phonons), and temperature-dependent energy level populations due to the CEF 15 The phonon contribution was represented by the measured $_{\rm lat}$ of LaO s $_4$ Sb $_{12}$, an isostructural reference compound without f-electrons, for all values of x. This pro-

cedure was validated by reproducing the results of A be et al. with LaO $s_4{\rm Sb}_{12}$ instead of LaRu4Sb12; as expected, the lat data of the two compounds appear to be nearly identical. The CEF contribution to (T) consists of two terms, representing magnetic exchange and aspherical Coulomb scattering, which were assumed to be equally important when thing the data. Just as it was possible to t (T) of PrO ${\rm sSb}_{12}$ with either a $_3$ or a $_1$ ground state, all of the Pr(O ${\rm s}_1$ x Rux)4Sb12 data were indierent to the choice of either ground state. The splitting between the ground state and the rest excited state (always a $_5$ triplet) was also nearly identical for ts with either ground state for a particular value of x.

ts with either ground state for a particular value of x. In the interest of sim plicity, for the (T) data, only the splitting between $_3$ and $_5$, $E_{3\ 5}$, is shown in Fig. 8. The tused to calculate $E_{3\ 5}$ for x=0:15 is shown in Fig. 7 (b). It is evident that (H) measurements will be required to elucidate the CEF ground state from transport measurements. 15

It is unclear what e ect the CEF ground state may have on the superconductivity in $Pr(Os_1 \times Ru_x)_4Sb_{12}$. From a physical point of view, it is reasonable that an abrupt change in the ground state would produce an equally abrupt change in the physical properties. However, it is di cult to conceive of a mechanism for this occurrence in the context of the LLW theory, since it is based on the interaction of the atom ic lattice with a rare earth ion. If there is not an abrupt change in the lattice structure, one should not expect an abrupt change in the CEF ground state. It is therefore far m ore reasonable to consider a constant ground state, with the excited state varying as the Ru substitution changes the spacing of the atom s in the skutterudite lattice. The present data are most consistent with a constant 3 ground state, with the exception of the x = 0.9 and x = 1 data. However, when x is in the region 0.2 x 0.75 a $_3$ energy level scheme is the only one which reasonably ts the dc(T;x) data. On the other hand, the possibility cannot be ruled out that this deep in a substituted system, a CEF analysis in the tradition of LLW may be unreliable due to the distribution of the two substituents (Or and Ru) in the near neighbor environment of each Pr^{3+} ion. The gradual m etam orphosis of the dc data does suggest that the CEF param eters are also changing gradually, but this may be misleading. Further experim ents as well as theoretical analysis will be necessary to com pletely reveal the CEF ground state and its relationship to the superconductivity.

V. SUMMARY

The superconducting critical tem perature T_{c} and crystalline electric $\,$ eld (CEF) parameters of single crystals of Pr(O s_{1} $_{x}$ Ru $_{x}$) $_{4}$ Sb $_{12}$ have been deduced through measurements of (T) and (T) for 0 $\,$ x $\,$ 1 . The superconductivity, which is present for all values of x, exhibits a change in the sign of the slope in $T_{\text{c}}\left(x\right)$ near

x = 0.6. The CEF ground state m ay also change from a $_3$ ground state to a $_1$ ground state near this concentration, although m ore measurements are necessary to con $\,$ m this possibility. It is possible that the crossover from heavy ferm ion superconductivity that m ay be mediated by quadrupolar interactions to nearly BCS superconductivity occurs at this 'pseudocritical' concentration x_{pc} = 0.6.

D epartm ent of Energy Grant No.DE-FG03-86ER-45230, the U.S.National Science Foundation Grant No.DMR-00-72125, and the NEDO International Joint Research Program .

discussions. This research was supported by the U.S.

A cknow ledgem ents

We would like to thank S.K.K im and D.T.Walker for experimental assistance, and E.D.Bauer for useful

¹ E.D. Bauer, N.A. Frederick, P.-C. Ho, V.S. Zapf, and M.B. Maple, Phys. Rev. B 65, 100506 (R) (2002).

M.B.Maple, P.C.Ho, V.S.Zapf, N.A.Frederick, E.D. Bauer, W.M.Yuhasz, F.M.Woodward, and J.W.Lynn, J.Phys.Soc.Jpn.71 Suppl., 23 (2002).

Y.Aoki, T.Namiki, S.Ohsaki, S.R.Saha, H.Sugawara, and H.Sato, J.Phys.Soc.Jpn.71, 2098 (2002).

⁴ M.Kohgi, M.Iwasa, M.Nakajima, N.Metoki, S.Araki, N. Bernhoeft, J.M. Mignot, A.Gukasov, H.Sato, Y.Aoki, and H.Sugawara (unpublished).

⁵ K. Takegahara, H. Harima, and A. Yanase, J. Phys. Soc. Jpn. 70, 1190 (2001).

⁶ D.E. MacLaughlin, J.E. Sonier, R.H. Hener, O.O. Bernal, B.-L. Young, M.S. Rose, G.D. Morris, E.D. Bauer, T.D.Do, and M.B. Maple, Phys. Rev. Lett. 89, 157001 (2002).

H. Kotegawa, M. Yogi, Y. Imamura, Y. Kawasaki, G. q. Zheng, Y. Kitaoka, S. Ohsaki, H. Sugawara, Y. Aoki, and H. Sato, Phys. Rev. Lett. 90, 027001 (2003).

⁸ M.B.Maple, P.-C. Ho, N.A. Frederick, V.S. Zapf, W.M. Yuhasz, and E.D. Bauer, Acta Physica Polonica B 34, 919 (2003).

⁹ R.Vollmer, A.Fait, C.P. eiderer, H.v.Lohneysen, E.D. Bauer, P.-C. Ho, V.S. Zapf, and M.B. Maple, Phys. Rev. Lett. 90, 057001 (2003).

N. O eschler, P. G egenwart, F. Steglich, N. A. Frederick, E. D. Bauer, and M. B. Maple, Acta Physica Polonica B 34,959 (2003).

¹¹ K. Izawa, Y. Nakajima, J. Goryo, Y. Matsuda, S. Osaki, H. Sugawara, H. Sato, P. Thalmeier, and K. Maki, Phys. Rev. Lett. 90, 117001 (2003).

P.-C. Ho, V. S. Zapf, E. D. Bauer, N. A. Frederick, and M. B. Maple, Int. J. Mod. Phys. B 16, 3008 (2002).

¹³ P.-C. Ho, N. A. Frederick, V. S. Zapf, E. D. Bauer, T. D. Do, M. B. Maple, A. D. Christianson, and A. H. Lacerda, Phys. Rev. B 67, 180508 (R) (2003).

N. O eschler, F. W eickert, P. G egenwart, P. T halm eier, F. Steglich, E. D. Bauer, and M. B. Maple, Phys. Rev. B (2003), submitted.

¹⁵ N.A. Frederick and M.B.Maple, J.Phys.: Condens.Matter 15, 4789 (2003).

¹⁶ T. Tayama, T. Sakakibara, K. K itam i, M. Yokoyama, K. Tenya, H. Am itsuka, D. Aoki, Y. Onuki, and Z. K letowski, J. Phys. Soc. Jpn. 70, 248 (2001).

¹⁷ N. Takeda and M. Ishikawa, J. Phys. Soc. Jpn. 69, 868 (2000).

¹⁸ K.Abe, H.Sato, T.D.Matsuda, T.Namiki, H.Sugawara, and Y.Aoki, J.Phys.: Condens.Matter 14, 11757 (2002).

M. Yogi, H. Kotegawa, Y. Im amura, G. q. Zheng, Y. Kitaoka, H. Sugawara, and H. Sato, cond-mat/0303569, (2003).

D.J.Braun and W. Jeitschko, J. Less-Common Met. 72, 147 (1980).

V.S.Zapf, R.P.Dickey, E.J.Freem an, C.Sirvent, and M.B.Maple, Phys. Rev. B 65, 024437 (2001).

P. G. Pagliuso, R. Movshovich, A. D. Bianchi, M. Nicklas, N. O. Moreno, J. D. Thompson, M. F. Hundley, J. L. Sarrao, and Z. Fisk, Physica B 312-313, 129 (2002).

²³ R. Movshovich, A. Bianchi, M. Jaime, M. F. Hundley, J.D. Thompson, N. Curro, P. C. Hammel, Z. Fisk, P. G. Pagliuso, and J. L. Sarrao, Physica B 312-313, 7 (2002).

²⁴ K.R.Lea, M.J.M.Leask, and W.P.Wolf, J.Phys.Chem. Solids 23, 1381 (1962).

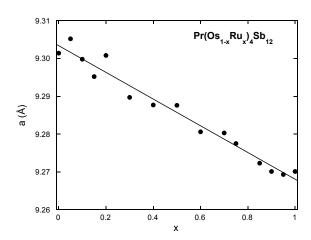


FIG .1: Lattice parameter a as a function of Ru concentration x. The solid line is a linear least squares t to a vs x.

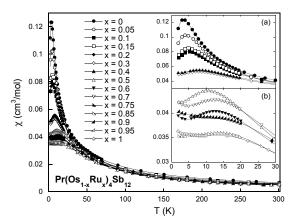


FIG. 2: dc m agnetic susceptibility $_{\rm dc}$ as a function of temperature T between 1.8 and 300 K for single crystals of Pr(O $_{\rm N}$ $_{\rm R}$ $_{\rm Ux}$) $_{\rm 4}$ Sb $_{\rm 12}$. Inset (a): $_{\rm dc}$ vs T between 1.8 and 30 K, showing the evolution of the peak due to crystalline electric elde ects for the Ru concentrations x = 0 to x = 0.4. The x = 0.2 sample has been removed for clarity. Inset (b): as inset (a), but for Ru concentrations x = 0.5 to x = 1. The samples with x = 0.75 and x = 0.95 were removed for clarity.

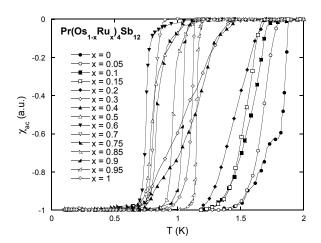


FIG. 3: ac magnetic susceptibility $_{\rm ac}$ as a function of temperature T between 0:1 and 2 K for single crystals of Pr(O s₁ $_{\rm x}$ Ru_x)₄Sb₁₂. The data have been normalized to 0 at T = 2 K and to 1 at T = 0 K for clarity.

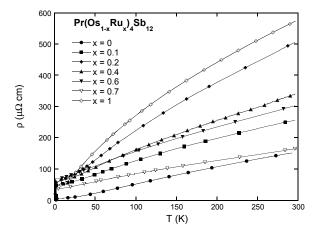


FIG. 4: Electrical resistivity as a function of temperature T between 0:4 and 300 K for single crystals of $Pr(Os_{1} _{x}Ru_{x})_{4}Sb_{12}$ with various values of x between 0 and 1. The samples with x=0.05, x=0.15, and x=0.9 were removed for clarity.

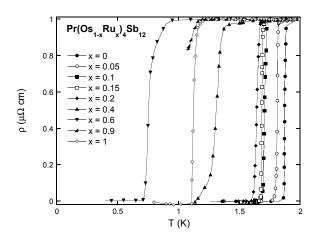


FIG .5: Electrical resistivity as a function of tem perature T between 0:4 and 2 K for single crystals of Pr(0 s₁ $_{x}$ Ru_x)₄Sb₁₂ with various values of x between 0 and 1, norm alized to their values at 2 K. The data for the sample with x = 0:7 is not shown because it did not superconduct down to the lowest tem perature measured (see text for details). Similarly, the superconducting transition for x = 0:9 is not complete due to the lim its of the experiment.

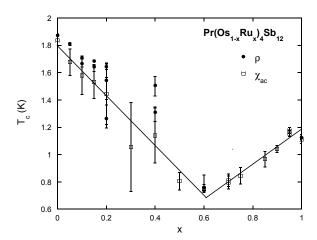


FIG. 6: Superconducting critical tem perature T_c vs Ru concentration x for Pr(O s_{1-x} Ru_x)₄Sb₁₂. Filled circles: T_c extracted from electrical resistivity . O pen squares: T_c determined from acm agnetic susceptibility T_c ac. The straight lines are guides to the eye.

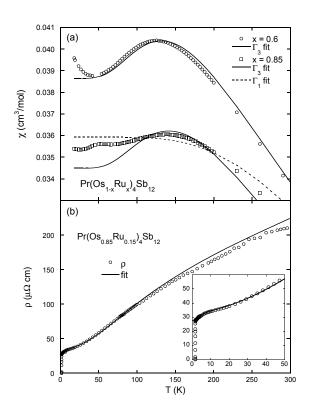


FIG. 7: Examples of CEF ts to the data. (a): dc magnetic susceptibility $_{\rm dc}$ (T) for x = 0.6 and x = 0.85 for Pr(O $_{\rm 1}$ $_{\rm K}$ Ru_x) $_{\rm 4}$ Sb $_{\rm 12}$. The solid lines are ts assuming a $_{\rm 3}$ doublet ground state and a $_{\rm 5}$ triplet rst excited state, and the dashed line is a tassuming a $_{\rm 1}$ singlet ground state and a $_{\rm 4}$ triplet rst excited state. (b): electrical resistivity (T) for x = 0.15 between 1 K and 300 K. The t is for a $_{\rm 3}$ ground state and a $_{\rm 5}$ rst excited state. Fits with a $_{\rm 1}$ ground state were qualitatively identical, and so are not shown (see text for details). Inset to (b): (T) for x = 0.15 between 1 K and 50 K, displaying the low-tem perature curvature in greater detail.

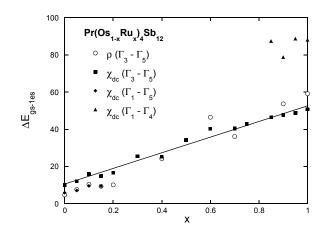


FIG. 8: The splitting between the ground state and rst excited state E $_{\rm gs\ 1es}$ vs Ru concentration x for Pr(O $_{\rm N}$ $_{\rm X}$ Rux) $_{\rm A}$ Sb12, calculated from ts of CEF equations to $_{\rm dc}$ (T) and (T), as described in the text. The solid line is a linear t to E $_{\rm gs\ 1es}$ for a $_{\rm 3}$ doublet ground state and a $_{\rm 5}$ triplet rst excited state calculated from the $_{\rm dc}$ (T) data. For x 0:15, a CEF energy level scheme with a $_{\rm 1}$ singlet ground state and a $_{\rm 5}$ rst excited state also provided a reasonable t to the $_{\rm dc}$ (T) data, while a $_{\rm 1}$ ground state with a $_{\rm 4}$ triplet rst excited state was also a possible energy level scheme e for x 0:85.

TABLE I: Physical properties of Pr(O $s_1 \times Ru_x$)₄Sb₁₂ compounds. x is the concentration of Ru; (300 K) is the electrical resistivity at 300 K; (0 K) is at 0 K extrapolated from CEF ts (see text); RRR is the residual resistivity ratio, dened as (300 K)= (0 K); % Sb is the percentage of the mass attributed to free Sb in $_{\rm dc}$ (T) assuming a $_3$ ground state; $x_{\rm LLW}$ and W are the Lea, Leask and W olf parameters; 24 and E $_{\rm a}$ $_{\rm b}$ is the energy dierence between ground state $_{\rm a}$ and rst excited state $_{\rm b}$.

The different better b.											
Х	(300 K)	(0 K)	RRR	% Sb	XL LW	W	E 3 5	x_{LLW}	W	E _{1 5}	E _{1 4}
	(cm) (cm)		3 ground state		(K)	₁ g.s.		(K)	(K)	
0	155	1.67	93	25.0	0:721	5 : 69	10.1	0.500	1.99	5.87	
0.05	235	18.7	13	15.1	0:720	6:38	12.1	0.484	1.47	7.08	
0.1	259	46.0	5.6	21.3	0:717	7:05	15.9	0.462	1.31	9.54	
0.15	215	27.0	0.8	15.6	0:718	7:00	14.9	0.452	1.11	9.43	İ
0.2	510	54.0	9.4	27.3	0:713	6:16	16.6				İ
0.3				0.8	0:707	7:48	25.5	Ì	ĺ	Ì	İ
0.4	343	58.2	5.9	20.2	0:702	6 : 43	25.2	Ì	ĺ	Ì	İ
0.5				4.9	0 : 687	6 : 06	34.2	Ì	ĺ	Ì	İ
0.6	305	67.4	4.5	6.6	0 : 675	5 : 75	40.3	Ì	ĺ	Ì	İ
0.7	166	34.8	4.8	10.1	0 : 663	4:81	40.4		ĺ		
0.75				17.2	0 : 669	5 : 54	42.8				
0.85				6.3	0 : 670	6 : 05	46.4	0:737	2.70		87.4
0.9	330	42.4	7.8	11.9	0:646	4:58	47.7	0:872	3.43		78.8
0.95				20.8	0 : 665	5 : 94	48.8	0:970	5.51		88.7
1	578	41.8	14	7.4	0 : 946	5 : 45	50.8	0:946	4.95		88.1